

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

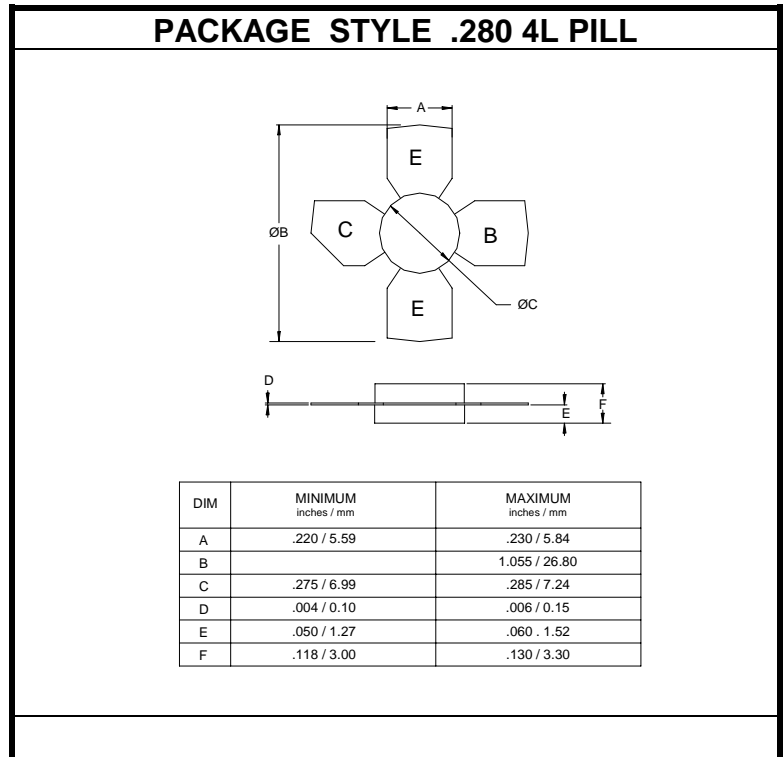
The **ASI MRF652S** is Designed for UHF large signal, amplifier Applications in FM equipment up to 512 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 10$  dB at 5.0 W/512 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	2.0 A
$V_{CBO}$	36 V
$V_{CER}$	16 V
$V_{EBO}$	4.0 V
$P_{DISS}$	25 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	200 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 25$ mA	16			V
$BV_{CES}$	$I_C = 25$ mA	36			V
$BV_{CBO}$	$I_C = 25$ mA	36			V
$BV_{EBO}$	$I_E = 5.0$ mA	4.0			V
$I_{CES}$	$V_{CE} = 15$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 200$ mA	10		150	---
$C_{ob}$	$V_{CB} = 15$ V $f = 1.0$ MHz		9.5	15	pF
$P_G$	$V_{CC} = 12.5$ V $P_{OUT} = 5.0$ W $f = 512$ MHz	10	11		dB
$\eta_c$		60	65		%